Abstracts

An accurate large-signal model for a high-efficient Si bipolar GSM power transistor

R.M. Heeres, H.A. Visser and M.P.J.G. Versleijen. "An accurate large-signal model for a high-efficient Si bipolar GSM power transistor." 2001 MTT-S International Microwave Symposium Digest 01.2 (2001 Vol. II [MWSYM]): 975-978 vol.2.

We present an accurate large-signal modelling approach for Si bipolar RF power transistors. An equivalent circuit model of a state of the art GSM power transistor (900 MHz, 3.5 V, 4 W, 70%) is constructed. The model is verified with accurate load pull measurements. Large-signal parameters (P/sub out/, G/sub T/, PAE) are predicted accurately.

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